

DIFFERENTIAL MEASUREMENTS FOR ENDPOINT SIGNAL ENHANCEMENT

ABSTRACT OF THE DISCLOSURE

A method for etching a layer is provided. A substrate is provided in a chamber. An etch plasma for etching a layer on the substrate is generated. Light from a first region of the chamber is measured to provide a first signal. Light from a second region of the chamber is measured to provide a second signal. The first signal with the second signal are compared to determine an etch endpoint.

FIG. 1

